

Features

- Operating voltage: 2.7V~5.5V
- Low power consumption
 - Operation: 25mA max. ($V_{CC}=5V$)
10mA max. ($V_{CC}=3V$)
 - Standby: 30 μ A max. ($V_{CC}=5V$)
10 μ A max. ($V_{CC}=3V$)
- Access time: 150ns max. ($V_{CC}=5V$)
250ns max. ($V_{CC}=3V$)
- 65536×8-bit of mask ROM
- Mask options: chip enable $\overline{CE}/\overline{OE1}/\overline{OE1}$ and output enable $\overline{OE}/\overline{OE}/\overline{NC}$
- TTL compatible inputs and outputs
- Tristate outputs
- Fully static operation
- 28-pin DIP/SOP package

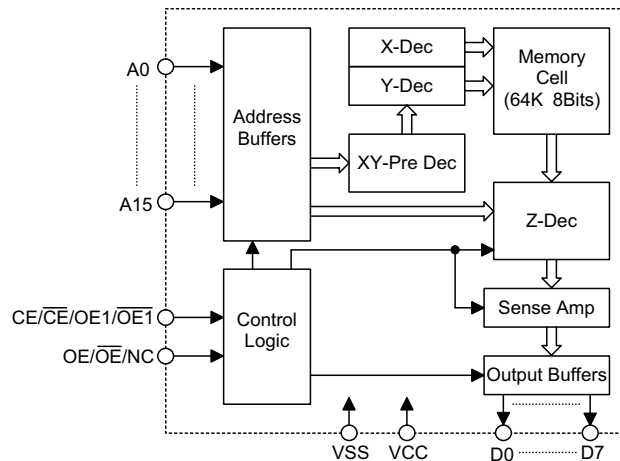
General Description

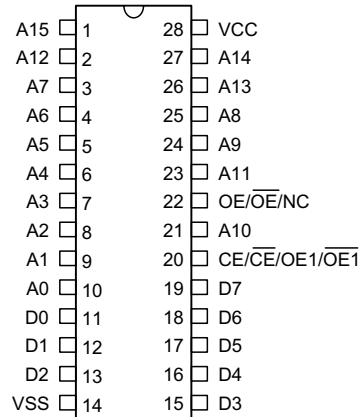
The HT23C512 is a read-only memory with high performance CMOS storage device whose 512K of memory is arranged into 65536 words by 8 bits.

For application flexibility, the chip enable and output enable control pins can be selected as active high or active low. This flexibility not only allows easy interface with most microprocessors, but also eliminates bus conten-

tion in multiple bus microprocessor systems. An additional feature of the HT23C512 is its ability to enter the standby mode whenever the chip enable ($\overline{CE}/\overline{OE}$) is inactive, thus reducing current consumption to below 30 μ A. The combination of these functions makes the chip suitable for high density low power memory applications.

Block Diagram



Pin Assignment


HT23C512
- 28 DIP-A/SOP-A

Pin Description

Pin Name	I/O	Description
A0~A15	I	Address inputs
D0~D7	O	Data outputs
CE/ \overline{CE} /OE1/ $\overline{OE1}$	I	Chip enable/Output enable input
OE/ \overline{OE} /NC	I	Output enable input
VSS	—	Negative power supply, ground
VCC	—	Positive power supply

Absolute Maximum Ratings

Supply Voltage-0.3V to 6V Storage Temperature-50°C to 125°C
 Input Voltage.....-0.3V to $V_{CC}+0.3V$ Operating Temperature.....-40°C to 85°C

Note: These are stress ratings only. Stresses exceeding the range specified under "Absolute Maximum Ratings" may cause substantial damage to the device. Functional operation of this device at other conditions beyond those listed in the specification is not implied and prolonged exposure to extreme conditions may affect device reliability.

D.C. Characteristics
Supply voltage: 2.7V~3.6V

Ta=-40°C to 85°C

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
		V _{CC}	Conditions				
V _{CC}	Operating Voltage	—	—	2.7	—	3.6	V
I _{CC}	Operating Current	3V	O/P Unload, f=5MHz	—	—	10	mA
V _{IL}	Input Low Voltage	3V	—	V _{SS}	—	0.4	V
V _{IH}	Input High Voltage	3V	—	2.0	—	V _{CC}	V
V _{OL}	Output Low Voltage	3V	I _{OL} =2.1mA	—	—	0.4	V
V _{OH}	Output High Voltage	3V	I _{OH} =-0.4mA	2.4	—	V _{CC}	V

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
		V _{CC}	Conditions				
I _{LI}	Input Leakage Current	3V	V _{IN} =0 to V _{CC}	—	—	10	μA
I _{LO}	Output Leakage Current	3V	V _{OUT} =0 to V _{CC}	—	—	10	μA
I _{STB1}	Standby Current	3V	CE=V _{IL} , \overline{CE} =V _{IH}	—	—	500	μA
I _{STB2}	Standby Current	3V	CE ≤ 0.2V, \overline{CE} ≥ V _{CC} -0.2V	—	—	10	μA
C _{IN}	Input Capacitance (See Note)	—	f=1MHz	—	—	10	pF
C _{OUT}	Output Capacitance (See Note)	—	f=1MHz	—	—	10	pF

Note: These parameters are periodically sampled but not 100% tested.

Supply voltage: 4.5V~5.5V

Ta=−40°C to 85°C

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
		V _{CC}	Conditions				
V _{CC}	Operating Voltage	—	—	4.5	—	5.5	V
I _{CC}	Operating Current	5V	O/P Unload, f=5MHz	—	—	25	mA
V _{IL}	Input Low Voltage	5V	—	V _{SS}	—	0.8	V
V _{IH}	Input High Voltage	5V	—	2.2	—	V _{CC}	V
V _{OL}	Output Low Voltage	5V	I _{OL} =3.2mA	—	—	0.4	V
V _{OH}	Output High Voltage	5V	I _{OH} =−1mA	2.4	—	V _{CC}	V
I _{LI}	Input Leakage Current	5V	V _{IN} =0 to V _{CC}	—	—	10	μA
I _{LO}	Output Leakage Current	5V	V _{OUT} =0 to V _{CC}	—	—	10	μA
I _{STB1}	Standby Current	5V	CE=V _{IL} , \overline{CE} =V _{IH}	—	—	1.5	mA
I _{STB2}	Standby Current	5V	CE ≤ 0.2V, \overline{CE} ≥ V _{CC} -0.2V	—	—	30	μA
C _{IN}	Input Capacitance (See Note)	—	f=1MHz	—	—	10	pF
C _{OUT}	Output Capacitance (See Note)	—	f=1MHz	—	—	10	pF

Note: These parameters are periodically sampled but not 100% tested.

A.C. Characteristics

Ta=−40°C to 85°C

Symbol	Parameter	V _{CC} =2.7V~3.6V		V _{CC} =4.5V~5.5V		Unit
		Min.	Max.	Min.	Max.	
t _{CYC}	Cycle Time	250	—	150	—	ns
t _{AA}	Address Access Time	—	250	—	150	ns
t _{ACE}	Chip Enable Access Time	—	250	—	150	ns
t _{AOE}	Output Enable Access Time	—	150	—	80	ns
t _{OH}	Output Hold Time	—	—	10	—	ns
t _{OD}	Output Disable Time (See Note)	—	—	—	70	ns
t _{OE}	Output Enable Time (See Note)	—	—	10	—	ns

Note: These parameters are periodically sampled but not 100% tested.

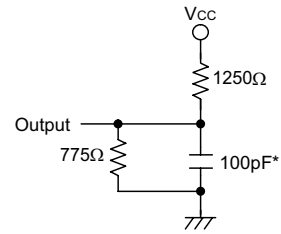
A.C. test conditions

Output load: see figure right

Input rise and fall time: 10ns

Input pulse levels: 0.4V to 2.4V

Input and output timing reference levels:
0.8V and 2.0V ($V_{CC}=5V$), 1.5V ($V_{CC}=3V$)



* Including scope and jig
Output load circuit

Functional Description

The HT23C512 has two modes, namely data read mode and standby mode, controlled by $\overline{CE}/\overline{CE}/\overline{OE1}/\overline{OE1}$ and $\overline{OE}/\overline{OE}/\overline{NC}$ inputs.

• Standby mode

The HT23C512 has lower current consumption, controlled by the chip enable input ($\overline{CE}/\overline{CE}$). When a low/high level is applied to the $\overline{CE}/\overline{CE}$ input regardless of the output enable ($\overline{OE}/\overline{OE}/\overline{NC}$) states, the chip will enter the standby mode.

• Data read mode

When both the chip enable ($\overline{CE}/\overline{CE}/\overline{OE1}/\overline{OE1}$) and the output enable ($\overline{OE}/\overline{OE}/\overline{NC}$) are active, the chip is in data read mode. Otherwise, active $\overline{CE}/\overline{CE}$ and inactive $\overline{OE}/\overline{OE}/\overline{NC}$ result in deselect mode. The output will remain in Hi-Z state.

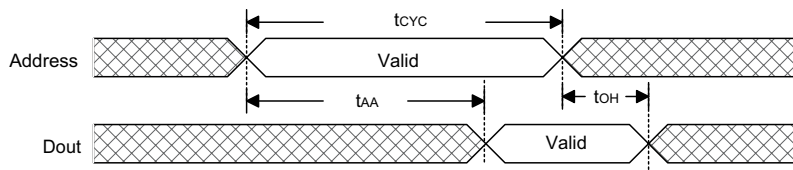
Operation Truth Table

Mode	$\overline{CE}/\overline{CE}$	$\overline{OE}/\overline{OE}$	A0~A15	D0~D7
Read	H/L	H/L	Valid	Data Out
Deselect	H/L	L/H	X	High Z
Standby	L/H	X	X	High Z

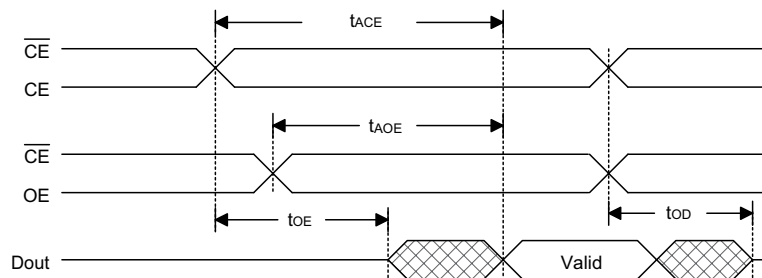
Note: H= V_{IH} , L= V_{IL} , X= V_{IH} or V_{IL}

Timing Diagrams

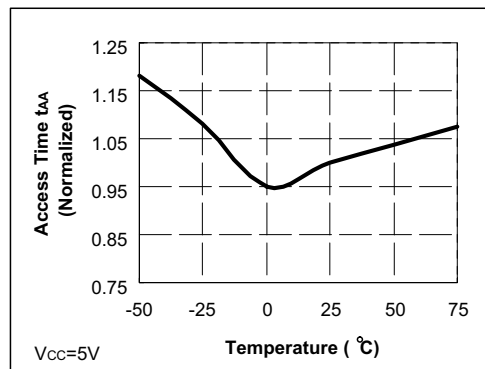
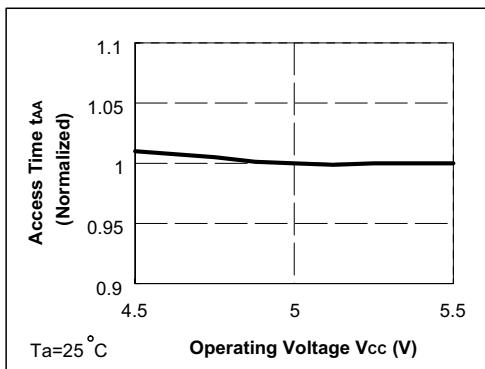
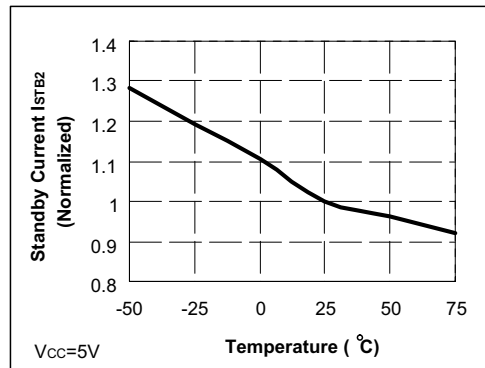
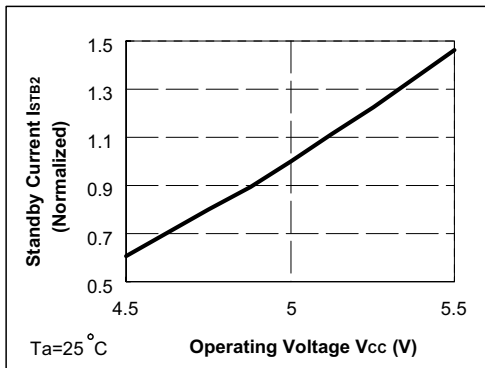
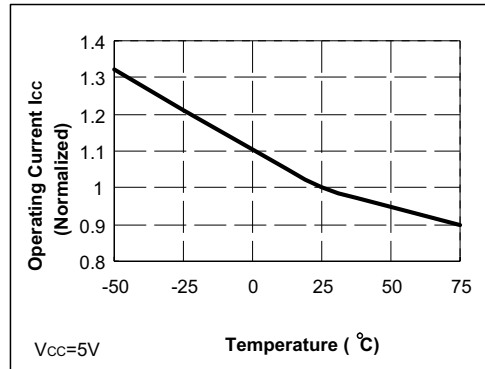
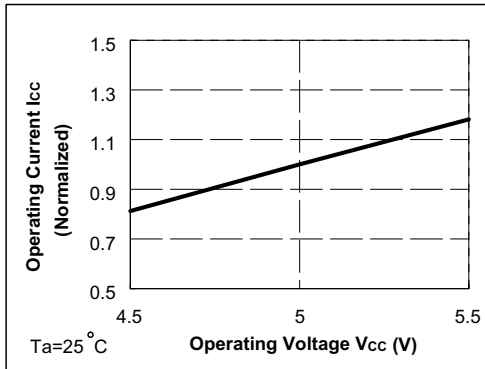
- Propagation delay due to address ($\overline{CE}/\overline{CE}/\overline{OE1}/\overline{OE1}$ and $\overline{OE}/\overline{OE}$ are active)

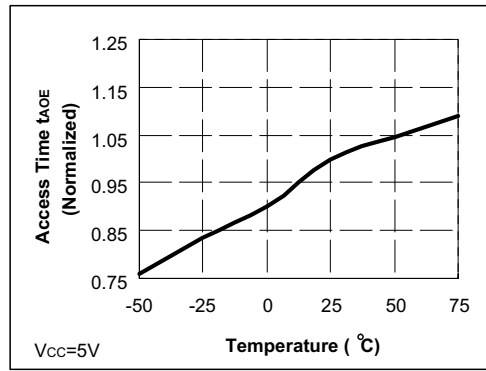
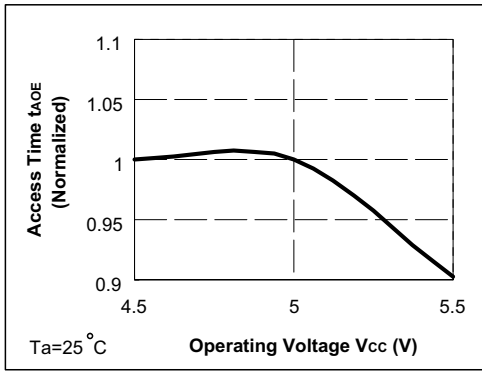
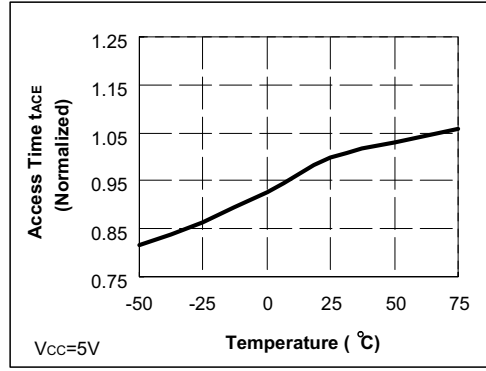
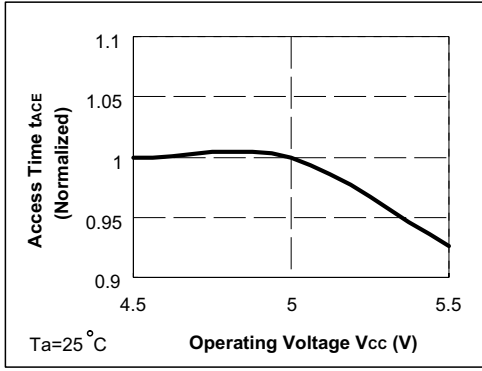


- Propagation delay due to chip enable and output enable (address valid)



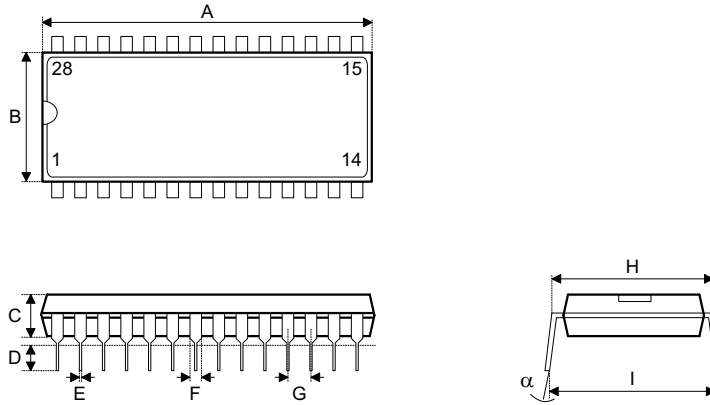
Characteristic Curves





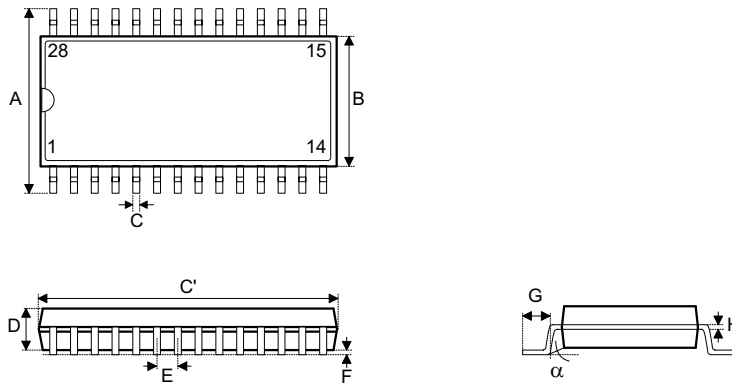
Package Information

28-pin DIP (600mil) outline dimensions



Symbol	Dimensions in mil		
	Min.	Nom.	Max.
A	1445	—	1465
B	535	—	555
C	145	—	155
D	125	—	145
E	16	—	20
F	50	—	70
G	—	100	—
H	595	—	615
I	635	—	670
α	0°	—	15°

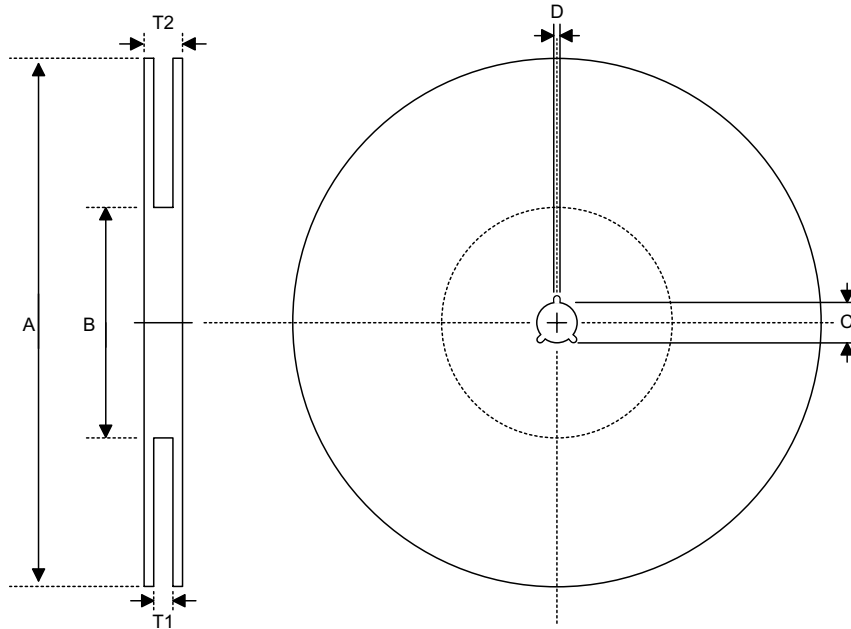
28-pin SOP (300mil) outline dimensions



Symbol	Dimensions in mil		
	Min.	Nom.	Max.
A	394	—	419
B	290	—	300
C	14	—	20
C'	697	—	713
D	92	—	104
E	—	50	—
F	4	—	—
G	32	—	38
H	4	—	12
α	0°	—	10°

Product Tape and Reel Specifications

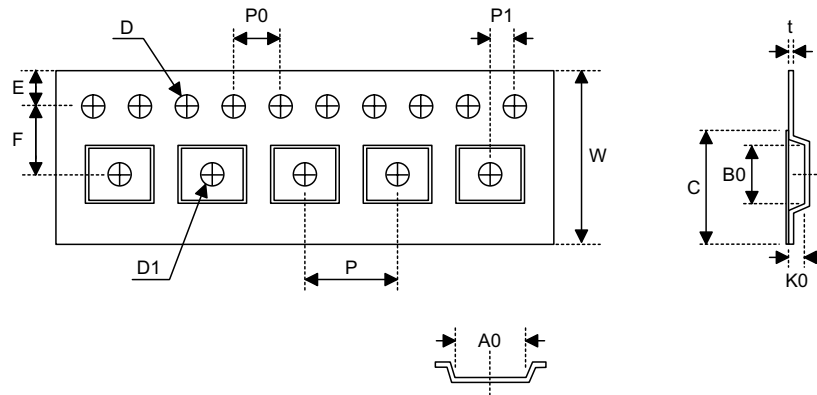
Reel dimensions



SOP 28W (300mil)

Symbol	Description	Dimensions in mm
A	Reel Outer Diameter	330±1.0
B	Reel Inner Diameter	62±1.5
C	Spindle Hole Diameter	13.0+0.5 -0.2
D	Key Slit Width	2.0±0.5
T1	Space Between Flange	24.8+0.3 -0.2
T2	Reel Thickness	30.2±0.2

Carrier tape dimensions



SOP 28W (300mil)

Symbol	Description	Dimensions in mm
W	Carrier Tape Width	24.0±0.3
P	Cavity Pitch	12.0±0.1
E	Perforation Position	1.75±0.1
F	Cavity to Perforation (Width Direction)	11.5±0.1
D	Perforation Diameter	1.5+0.1
D1	Cavity Hole Diameter	1.5+0.25
P0	Perforation Pitch	4.0±0.1
P1	Cavity to Perforation (Length Direction)	2.0±0.1
A0	Cavity Length	10.85±0.1
B0	Cavity Width	18.34±0.1
K0	Cavity Depth	2.97±0.1
t	Carrier Tape Thickness	0.35±0.01
C	Cover Tape Width	21.3

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